

METHODS OF MANUFACTURE FOR A LOW CONTROL
VOLTAGE SWITCH

CROSS-REFERENCE TO RELATED APPLICATIONS

nn The present application is a divisional application of U.S. Patent Application
Serial No. 10/391,259, ^{filed March 18, 2003, now US patent No 6,730,953} which claims the priority of U.S. Provisional Patent Application
Serial No. 60/410647, filed on September 13, 2002, which is herein incorporated in its
entirety by reference.

FIELD OF INVENTION

The present invention relates generally to switch devices, and more particularly to
solid-state switch devices.

BACKGROUND OF THE INVENTION

Conventional switch devices operate to control the path on which a signal travels.
In general, there are two basic types of switch devices in use: electromechanical and solid
state. All switches are considered active devices, in that some sort of power supply is
required in order to function properly. In electromechanical switches, a contact is
provided that physically changes position during the switching process. Solid-state
switches do not contain any moving parts and instead use some kind of semiconductor
device for the switching process, which are basically either diodes or transistors. In
general, diode switches sense current as a control input while switches comprised of
transistors sense voltages as control inputs. One example of a transistor-based switch is
comprised of a plurality of field effect transistors (FETs). FET switches are generally
known to be utilized in connection with high frequency signal transmission, for example,
radio frequency (RF).

In general, a FET switch is in an ON state (very low resistance) allowing any
signal to pass from the drain to the source of the FET until a control voltage of a